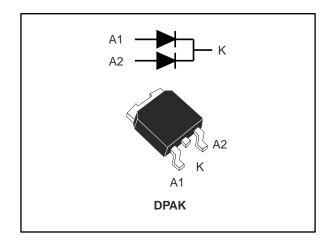
STTH602C-Y



Automotive ultrafast recovery diode

Datasheet - production data



Features



- AEC-Q101 qualified
- Suited for SMPS
- Low losses
- Low forward and reverse recovery time
- High surge current capability
- High junction temperature
- PPAP capable

Description

This dual center tap diode is suited for switch mode power supplies and high frequency DC to DC converters.

Packaged in DPAK, this device is intended for use in low voltage high frequency inverters, freewheeling and polarity protection for automotive applications.

Table 1: Device summary

Symbol	Value
I _{F(AV)}	2 x 3 A
V_{RRM}	200 V
V _F (typ.)	0.80 V
T _j (max.)	175 °C
T _{rr} (typ.)	14 ns

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1 Characteristics

Table 2: Absolute ratings (limiting values at 25 °C, unless otherwise specified)

Symbol	Parameter	Value	Unit	
V _{RRM}	Repetitive peak reverse voltage		200	V
I _{F(RMS)}	Forward rms current		11	Α
	Average forward current	T _c = 160 °C	3	۸
I _{F(AV)}	δ = 0.5, square wave	T _c = 155 °C	6	Α
I _{FSM}	Surge non repetitive forward current	60	Α	
T _{stg}	Storage temperature range	-65 to +175	°C	
Tj	Operating junction temperature range -40 to			°C

Table 3: Thermal parameters

Symbol	Parameter	Max. value	Unit	
D lunction to coop		Per diode	5	
R _{th(j-c)}	Junction to case	Per device	3	°C/W
R _{th(c)}	Coupling		1	

When the two diodes 1 and 2 are used simultaneously:

 $\Delta T_i(\text{diode 1}) = P \text{ (diode 1)} \times R_{\text{th(i-c)}} \text{ (Per diode)} + P \text{ (diode 2)} \times R_{\text{th(c)}}$

Table 4: Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
1 (1)	I _R ⁽¹⁾ Reverse leakage current	T _j = 25 °C	V V	ı		3	μΑ
IR ¹⁷		T _j = 125 °C	$V_R = V_{RRM}$	ı	3	30	
	V _F ⁽²⁾ Forward voltage drop	T _j = 25 °C	I _F = 3 A	-	0.98	1.1	
V ₁₋ (2)		T _j = 150 °C		-	8.0	0.95	V
VFI		T _j = 25 °C		ı	1.1	1.25	V
		T _j = 150 °C	I _F = 6 A	1	0.9	1.05	

Notes:

 $^{(1)}$ Pulse test: t_p = 5 ms, δ < 2%

 $^{(2)} Pulse$ test: t_p = 380 $\mu s, \, \delta < 2\%$

To evaluate the conduction losses, use the following equation:

 $P = 0.85 \text{ x } I_{F(AV)} + 0.033 \text{ x } I_{F^2(RMS)}$

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Table 5: Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{rr} Reverse recovery time	Poverse recovery time	$I_F = 1 \text{ A}, \\ dI_F/dt = -100 \text{ A/}\mu\text{s}, \\ V_R = 30 \text{ V}, T_j = 25 \text{ °C}$	ı	14	20	2
	I _F = 1 A, dI _F /dt = -50 A/µs, V _R = 30 V, T _j = 25 °C	ı	21	30	ns	
I _{RM}	Reverse recovery current	I _F = 3 A, dI _F /dt = 200 A/μs, V _R = 160 V, T _j = 125 °C	-	4	5.5	Α
t _{fr}	Forward recovery time	I _F = 3 A, dI _F /dt = 200 A/μs V _{FR} = 1.1 x V _{Fmax} , T _j = 25 °C	-	24		ns
V _{FP}	Forward recovery voltage	I _F = 3 A, dI _F /dt = 200 A/μs, T _j = 25 °C	-	3.7		V

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1.1 Characteristics (curves)

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Figure 1: Peak current versus duty cycle (per diode)

Figure 2: Forward voltage drop versus forward

Figure 3: Forward voltage drop versus forward current (maximum values, per diode)

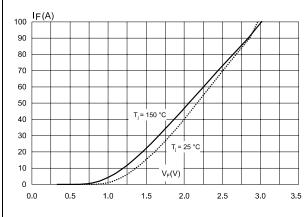


Figure 4: Relative variation of thermal impedance junction to case versus pulse duration (per diode)

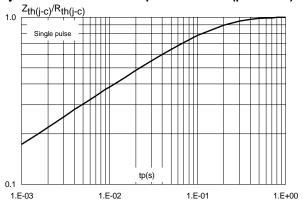


Figure 5: Junction capacitance versus reverse applied voltage (typical values, per diode)

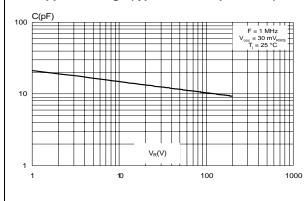
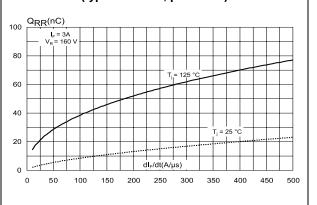


Figure 6: Reverse recovery charges versus dl_F/dt (typical values, per diode)



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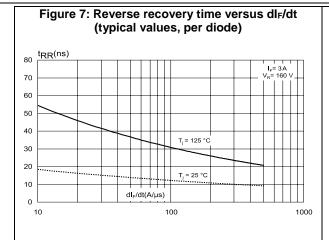


Figure 8: Reverse recovery current versus dl_F/dt (typical values, per diode)

10

10

1 | IRM(A)

10

1 | I_R = 3A

1 | I_R = 160 | I_R = 160 | I_R = 125 °C

4 | I_R = 160 | I_R = 125 °C

1 | I_R = 125 °C

2 | I_R = 160 | I_R = 160 | I_R = 125 °C

4 | I_R = 160 | I

Figure 9: Dynamic parameters versus junction temperature

QRR; |RM[Tj]/QRR; |RM[Tj = 125 °C]

1.4

1.2

VR= 160 V

1.0

0.8

0.6

0.4

0.2

0.0

25

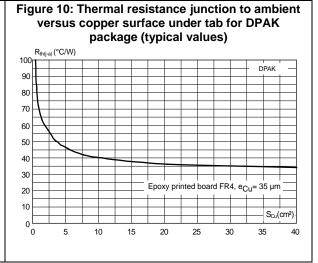
50

75

100

125

150



Package information STTH602C-Y

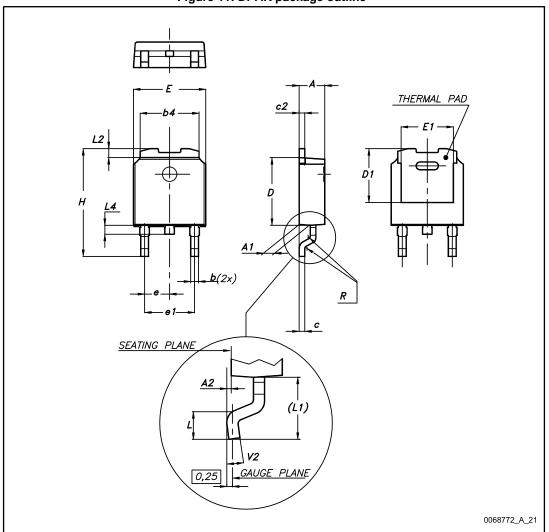
2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK® is an ST trademark.

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)

2.1 DPAK package information

Figure 11: DPAK package outline

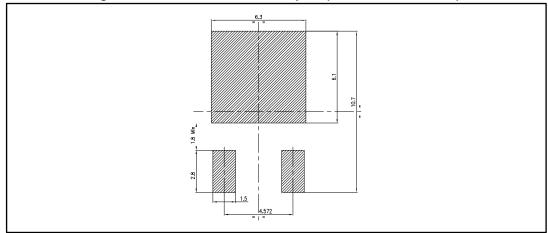


STTH602C-Y Package information

Table 6: DPAK mechanical data

	Dimensions					
Dim.		Millimeters			Inches	
	Min.	Тур.	Max.	Min.	Тур.	Max.
А	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
b	0.64		0.90	0.025		0.035
b4	5.20		5.40	0.205		0.213
С	0.45		0.60	0.018		0.024
c2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
D1	4.95	5.10	5.25	0.195	0.201	0.207
Е	6.40		6.60	0.252		0.260
E1	5.10	5.20	5.30	0.201	0.205	0.209
е	2.16	2.28	2.40	0.085	0.090	0.094
e1	4.40		4.60	0.173		0.181
Н	9.35		10.10	0.368		0.398
L	1.00		1.50	0.039		0.059
(L1)	2.60	2.80	3.00	0.102	0.110	0.118
L2	0.65	0.80	0.95	0.026	0.031	0.037
L4	0.60		1.00	0.024		0.039
R		0.20			0.008	
V2	0°		8°	0°		8°

Figure 12: DPAK recommended footprint (dimensions are in mm)



Ordering information STTH602C-Y

3 Ordering information

Table 7: Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STTH602CBY-TR	STTH6 02CBY	DPAK	0.30 g	2500	Tape and reel

4 Revision history

Table 8: Document revision history

Date	Revision	Changes
24-Oct-2012	1	First issue.
16-Mar-2017	2	Updated <i>Table 3: "Thermal parameters"</i> . Minor text changes.

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